ABSTRACT

STABILITY OF THE S-N BOND IN S-NITROSOTHIOLS: COMPUTATIONAL AND EXPERIMENTAL APPROACH

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Marquette University, 2024

S-Nitrosothiols (RSNOs) are chemical compounds capable to transport nitric oxide (NO) and show promise in the treatment of cardiovascular diseases. RSNOs occur naturally *in-vivo*, and others have been synthesized *in-vitro* as potential drug candidates for NO transport and release. However, RSNOs are inherently unstable due to their weak S–N bond ($D_0(S-N)=25-30$ kcal/mol), so developing a deeper understanding of the factors influencing the RSNOs stability is crucial.

In Chapter 2, we investigated the substituent effect on the -SNO group properties. Substituting R– in RSNOs with more electro-donating character can stabilize the –SNO group according to the Natural Resonance Theory (NRT). But modeling the RSNOs is a complex task requiring usage of CCSD(T)/CBS_(Q-5) or CCSD(T)-F12a/CBS_(T-Q) methods with the inclusion of different corrections (core-valence(Δ CV), scalar relativistic(Δ SR), spin-spin coupling(Δ SO), and high order corrections(Δ HO)) to predict properties of RSNOs accurately, specifically r(S–N) and D₀(S-N). Here, H-SNO, H₃C-SNO, H₃Si-SNO were studied using high-level coupled cluster methods, CCSD(T)/CBS_(Q-5) and CCSD(T)-F12a,b,c/CBS_(T-Q), with various basis sets, *cc-pVnZ-F12* and *aug-cc-pV(n+d)Z* (where n=D, T, Q and 5 (for *aug-cc-pV(5+d)Z*) with the addition of various corrections to correlation effects (Δ CV, Δ SR, Δ SO, Δ HO). It was found that r(S–N) is longer in the cis-H₃Si-SNO and cis-H-SNO than in the cis-H₃C-SNO. Additionally, D₀(S-N) is higher in the cis-H₃C-SNO than in the cis-H-SNO and cis-H-SNO.

In Chapter 3, experimentally, Ph₃ SiSNO and i-Pr₃ SiSNO were synthesized and characterized at temperatures below -35 °C. These silicon-containing RSNOs are stable at -45 °C but begin to decompose above -41 °C. Variable-temperature NMR studies determined the rotational energy barrier for cis-trans isomerization of Ph₃ SiS¹⁵ NO to be approximately 8.60 kcal/mol, which is 3–4 kcal/mol lower than for carbon-substituted RSNOs. UV-Vis spectroscopy and TD-DFT calculations supported the formation of these compounds. The EPR spectroscopy at 77 K was used to study the relatively stable Ph₃ SiS⁻ and i-Pr₃ SiS⁻ radicals.

In Chapter 4, DFT and NBO analyses provided insights into the electronic origins of the observed instability of silicon-substituted RSNOs. Hyperconjugative interactions, specifically $n(S) \rightarrow \sigma^*(Si-H)$, play a crucial role in modulating the properties of the -SNO group. Deletion of these interactions led to a decrease in the S–N bond length (~0.05 Å) and an increase in bond dissociation energy, indicating that the silicon atom enhances interactions $n(S) \rightarrow \sigma^*(Si-H)$ that weakens the S–N bond strength. A correlation was established between the electronegativity of the substituent and the S–N bond strength; increase in electronegativity decreases the bond strength due to increased hyperconjugative $n(S) \rightarrow \sigma^*(R-X)$ interactions.

In Chapter 5, we are expanding investigation on the crucial influence of non-covalent interaction with σ -hole of Sulfur on stability of S-Nitrosothiols using the high-level ab initio and DFT methods. It was found that π systems can interact with -SNO group via σ -hole of sulfur. Such interaction promotes the partial double bond character in the S-N bond, or promotion of D resonance structure, and simultaneously reduces the ionic character of RS⁻/NO⁺ (which destabilizes the -SNO group). Additionally, our calculation predicts that in the protein environment interaction of π systems with σ -hole of -SNO group tends to profoundly effect on the -SNO group properties (electronic structure and reactivity).